

# 2SC6046

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

2SC6046 is a silicon NPN epitaxial type transistor designed with high collector current, low  $V_{CE(sat)}$ .

## FEATURE

High collector current

$$I_{C(MAX)} = 600\text{mA}$$

Low collector to emitter saturation voltage

$$V_{CE(sat)} < 0.3V_{max} (I_C=150\text{mA}, I_B=15\text{mA})$$

## APPLICATION

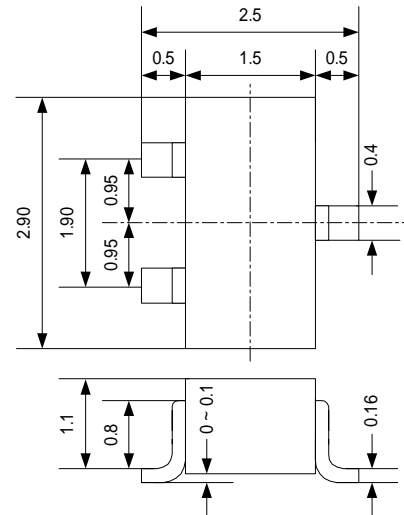
For switching application, small type motor drive application.

## MAXIMUM RATINGS (Ta.=25 °C)

記号	項目	定格値	単位
$V_{CEO}$	Collector to Emitter voltage	40	V
$V_{CBO}$	Collector to Base voltage	75	V
$V_{EBO}$	Emitter to Base voltage	6	V
$I_C$	Collector current	600	mA
$P_C$	Collector dissipation	200	mW
$T_j$	Junction temperature	+150	
$T_{stg}$	Storage temperature	-55 ~ +150	

## OUTLINE DRAWING

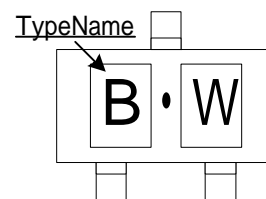
Unit: mm



## TERMINAL CONNECTOR

: BASE EIAJ: SC-59  
: EMITTER JEDEC: TO-236  
: COLLECTOR Resemblance

## MARKING

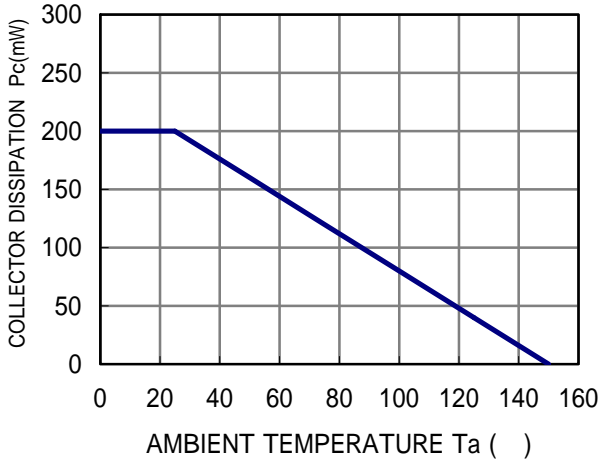


## ELECTRICAL CHARACTERISTICS (Ta.=25 °C)

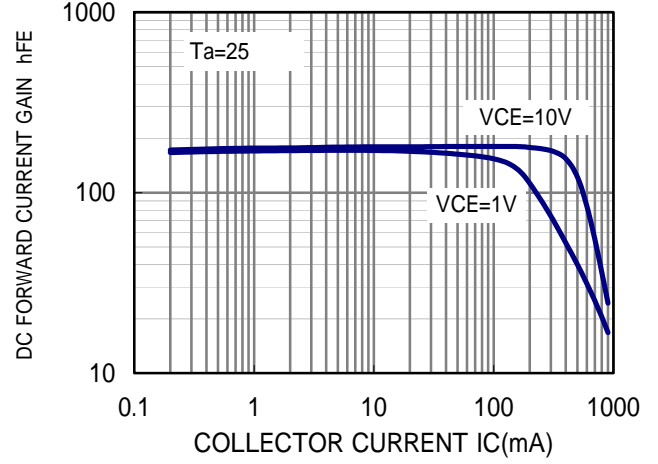
Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1\text{mA}, I_B=0$	40			V
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10\mu\text{A}, I_E=0$	75			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10\mu\text{A}, I_C=0$	6			V
$I_{CBO}$	Collector cut off current	$V_{CB}=60\text{V}, I_E=0$			100	nA
$I_{EBO}$	Emitter cut off current	$V_{EB}=3\text{V}, I_C=0$			100	nA
$h_{FE}$	DC forward current gain	$I_C=150\text{mA}, V_{CE}=10\text{V}$	100		300	---
$V_{CE(sat)}$	C to E saturation voltage	$I_C=150\text{mA}, I_B=15\text{mA}$			0.3	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6		1.2	V
$f_T$	Gain band width product	$I_E=-20\text{mA}, V_{CE}=20\text{V}, f=100\text{MHz}$		250		MHz
$C_{ob}$	Collector output capacitance	$V_{CB}=10\text{V}, f=1\text{MHz}$			8	pF

## TYPICAL CHARACTERISTICS

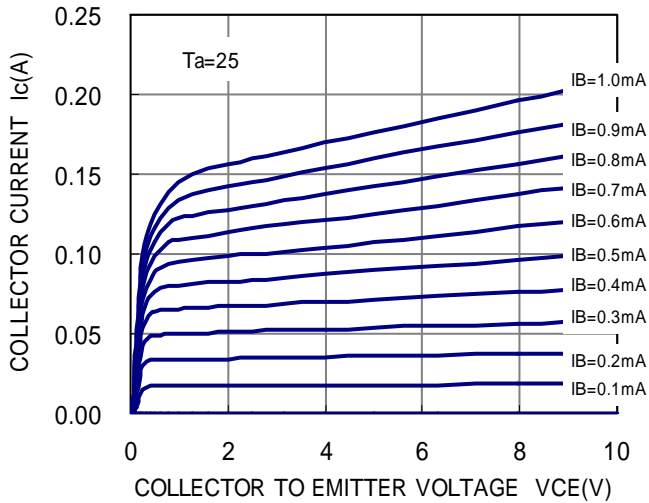
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



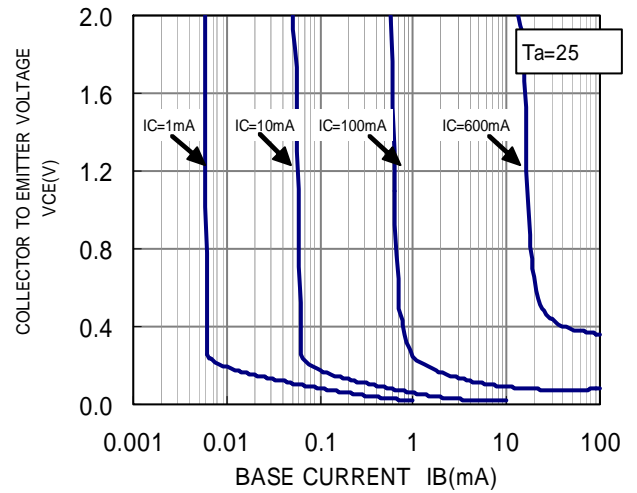
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



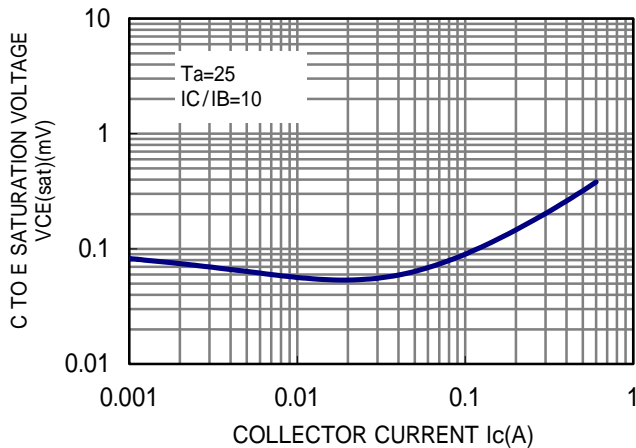
COMMON EMITTER OUTPUT



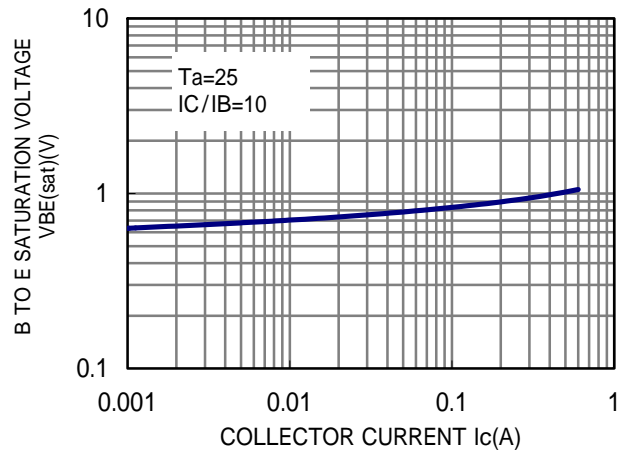
COLLECTOR TO EMITTER VOLTAGE VS. BASE CURRENT



C TO E SATURATION VOLTAGE VS. COLLECTOR CURRENT



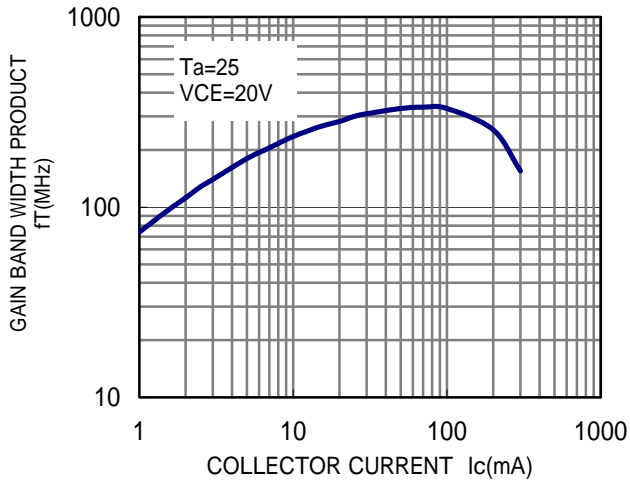
B TO E SATURATION VOLTAGE VS. COLLECTOR CURRENT



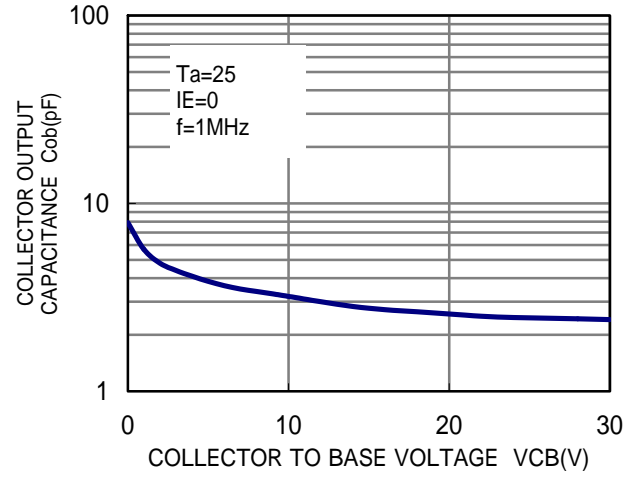
# 2SC6046

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

GAIN BAND WIDTH PRODUCT VS.  
COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS.  
COLLECTOR TO BASE VOLTAGE





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